

PNP Transistor, Low $V_{CE(sat)}$ 100 V, 2.0 A NSS1C200MZ4, NSV1C200MZ4

onsemi's e²PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC–DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free and are RoHS Compliant

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	–100	Vdc
Collector-Base Voltage	V_{CBO}	–140	Vdc
Emitter-Base Voltage	V_{EBO}	–7.0	Vdc
Base Current – Continuous	I_B	1.0	A
Collector Current – Continuous	I_C	2.0	A
Collector Current – Peak	I_{CM}	3.0	A

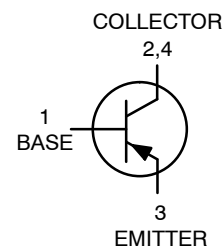
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 1)	800 6.5	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$ (Note 1)	155	$^\circ\text{C}/\text{W}$
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 2)	2.0 15.6	W mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$ (Note 2)	64	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR–4 @ 7.6 mm², 1 oz. copper traces.
2. FR–4 @ 645 mm², 1 oz. copper traces.

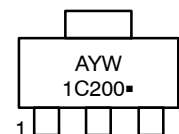
–100 VOLTS, 2.0 AMPS PNP LOW $V_{CE(sat)}$ TRANSISTOR



MARKING DIAGRAM

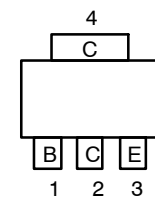


SOT-223
CASE 318E
STYLE 1



- A = Assembly Location
- Y = Year
- W = Work Week
- 1C200 = Specific Device Code
- = Pb–Free Package

PIN ASSIGNMENT



Top View Pinout

ORDERING INFORMATION

Device	Package	Shipping [†]
NSS1C200MZ4T1G NSV1C200MZ4T1G	SOT-223 (Pb–Free)	1000/ Tape & Reel
NSS1C200MZ4T3G	SOT-223 (Pb–Free)	4000/ Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NSS1C200MZ4, NSV1C200MZ4

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector - Emitter Breakdown Voltage ($I_C = -10 \text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	-100			Vdc
Collector - Base Breakdown Voltage ($I_C = -0.1 \text{ mAdc}$, $I_E = 0$)	$V_{(BR)CBO}$	-140			Vdc
Emitter - Base Breakdown Voltage ($I_E = -0.1 \text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	-7.0			Vdc
Collector Cutoff Current ($V_{CB} = -140 \text{ Vdc}$, $I_E = 0$)	I_{CBO}			-100	nAdc
Emitter Cutoff Current ($V_{EB} = -6.0 \text{ Vdc}$)	I_{EBO}			-50	nAdc
ON CHARACTERISTICS					
DC Current Gain (Note 3) ($I_C = -10 \text{ mA}$, $V_{CE} = -2.0 \text{ V}$) ($I_C = -500 \text{ mA}$, $V_{CE} = -2.0 \text{ V}$) ($I_C = -1.0 \text{ A}$, $V_{CE} = -2.0 \text{ V}$) ($I_C = -2.0 \text{ A}$, $V_{CE} = -2.0 \text{ V}$)	h_{FE}	150 120 80 50		360	
Collector - Emitter Saturation Voltage (Note 3) ($I_C = -0.1 \text{ A}$, $I_B = -0.010 \text{ A}$) ($I_C = -0.5 \text{ A}$, $I_B = -0.050 \text{ A}$) ($I_C = -1.0 \text{ A}$, $I_B = -0.100 \text{ A}$) ($I_C = -2.0 \text{ A}$, $I_B = -0.200 \text{ A}$)	$V_{CE(sat)}$			-0.040 -0.080 -0.125 -0.220	V
Base - Emitter Saturation Voltage (Note 3) ($I_C = -1.0 \text{ A}$, $I_B = -0.100 \text{ A}$)	$V_{BE(sat)}$			-0.950	V
Base - Emitter Turn-on Voltage (Note 3) ($I_C = -1.0 \text{ A}$, $V_{CE} = -2.0 \text{ V}$)	$V_{BE(on)}$			-0.850	V
Cutoff Frequency ($I_C = -100 \text{ mA}$, $V_{CE} = -5.0 \text{ V}$, $f = 100 \text{ MHz}$)	f_T		120		MHz
Input Capacitance ($V_{EB} = 3.0 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_{ibo}		200		pF
Output Capacitance ($V_{CB} = 10 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_{obo}		22		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle \leq 2%.

NSS1C200MZ4, NSV1C200MZ4

TYPICAL CHARACTERISTICS

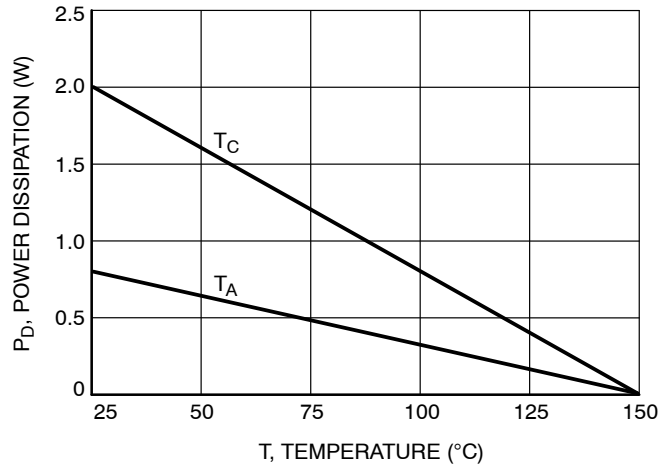


Figure 1. Power Derating

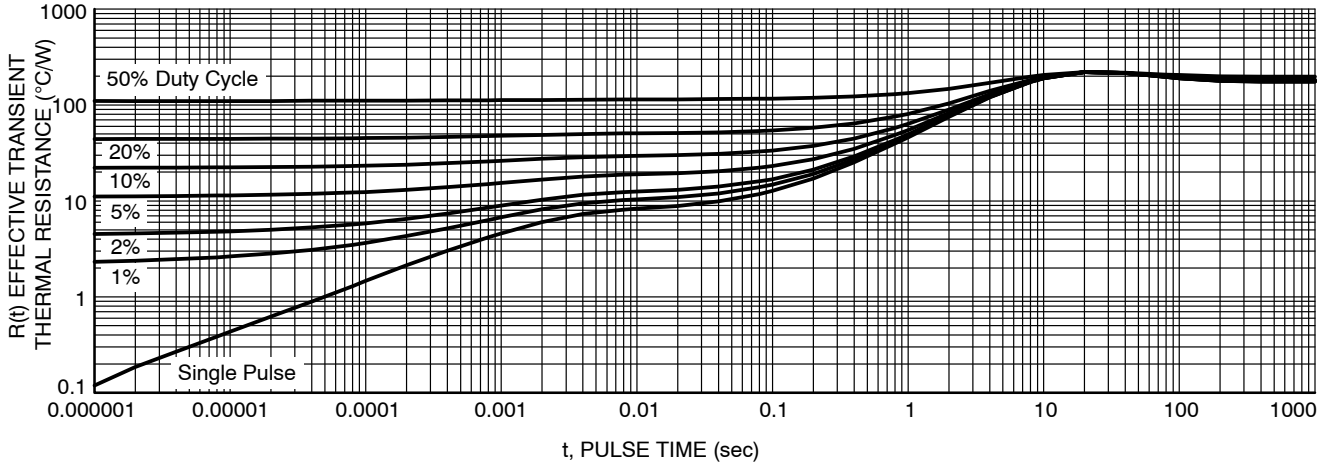


Figure 2. Thermal Resistance (FR-4 @ 7.6 mm², 1 oz. Cu trace)

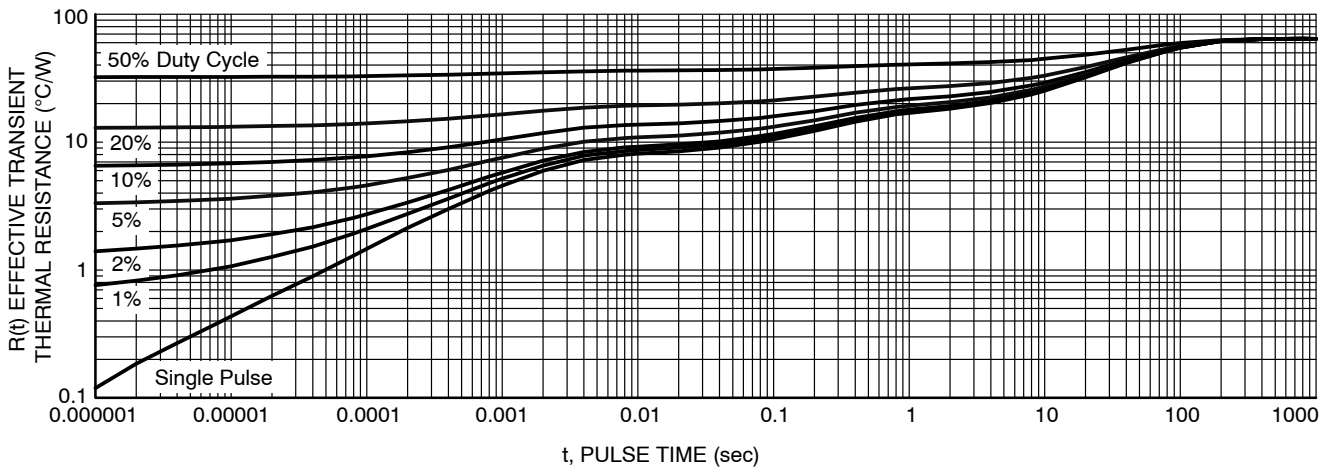


Figure 3. Thermal Resistance (FR-4 @ 645 mm², 1 oz. Cu trace)

NSS1C200MZ4, NSV1C200MZ4

TYPICAL CHARACTERISTICS

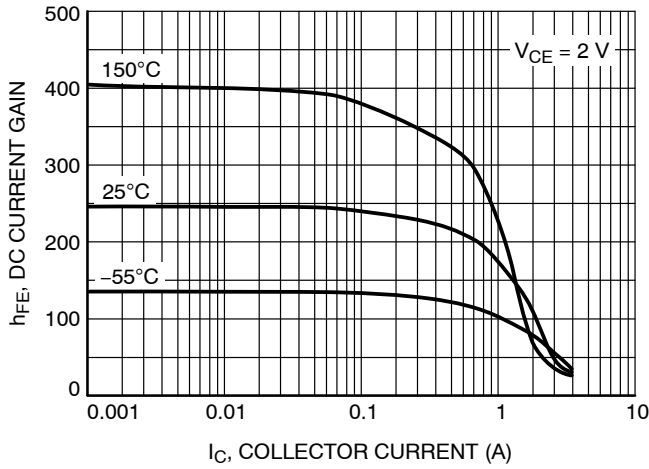


Figure 4. DC Current Gain

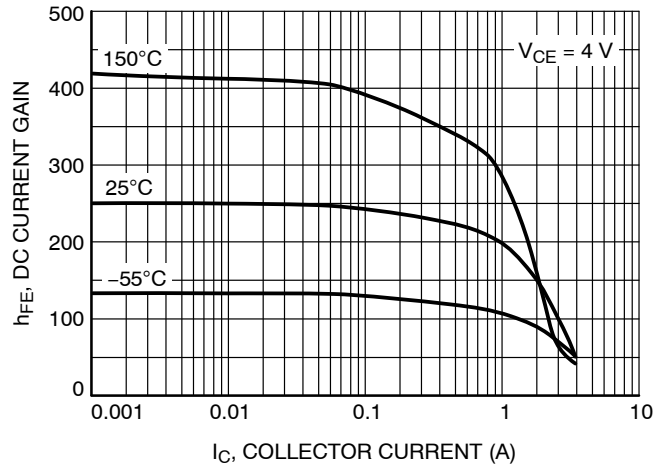


Figure 5. DC Current Gain

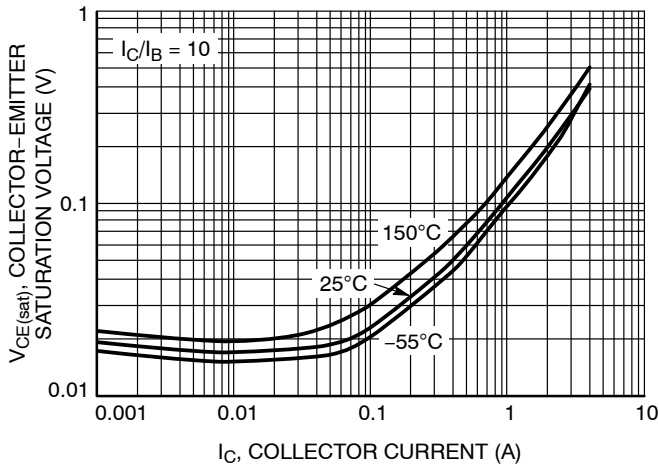


Figure 6. Collector-Emitter Saturation Voltage

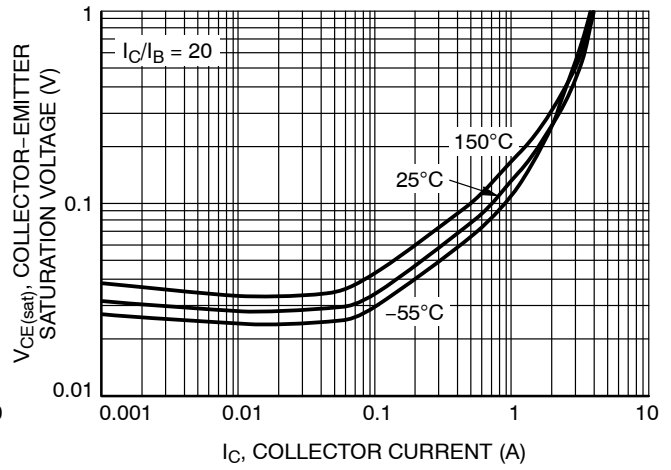


Figure 7. Collector-Emitter Saturation Voltage

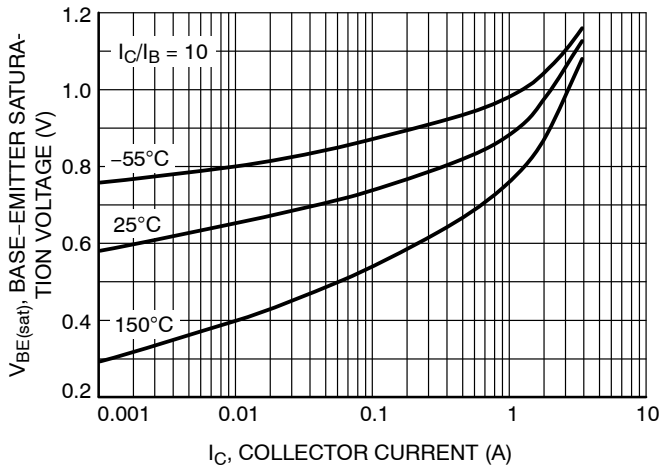


Figure 8. Base-Emitter Saturation Voltage

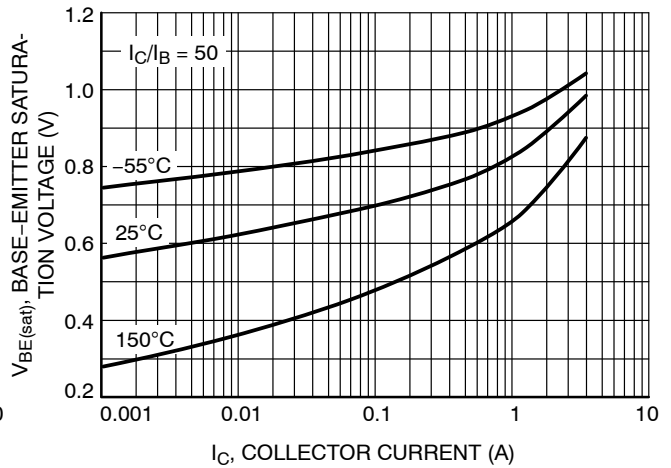


Figure 9. Base-Emitter Saturation Voltage

NSS1C200MZ4, NSV1C200MZ4

TYPICAL CHARACTERISTICS

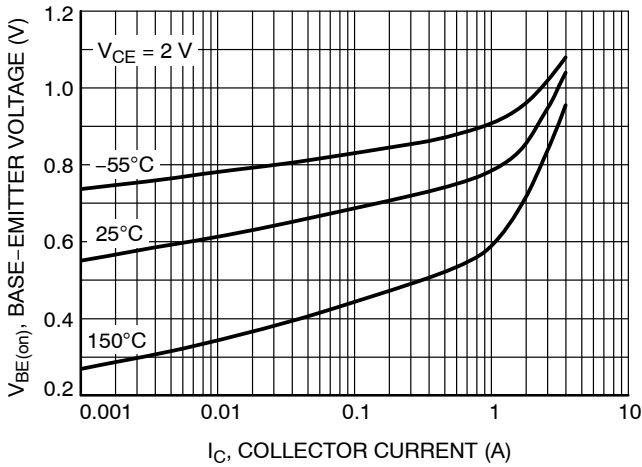


Figure 10. Base-Emitter Voltage

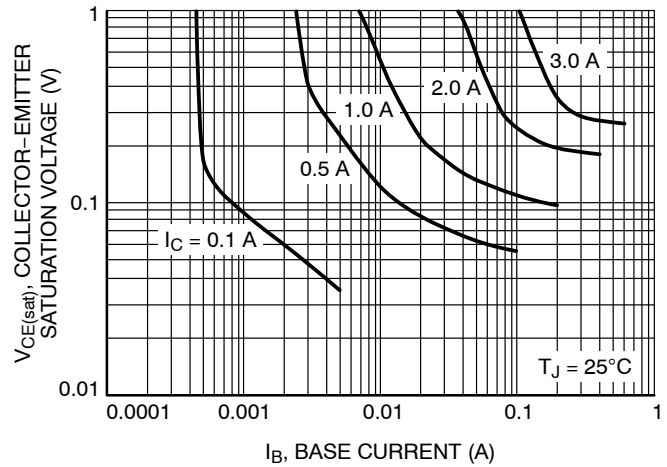


Figure 11. Collector Saturation Region

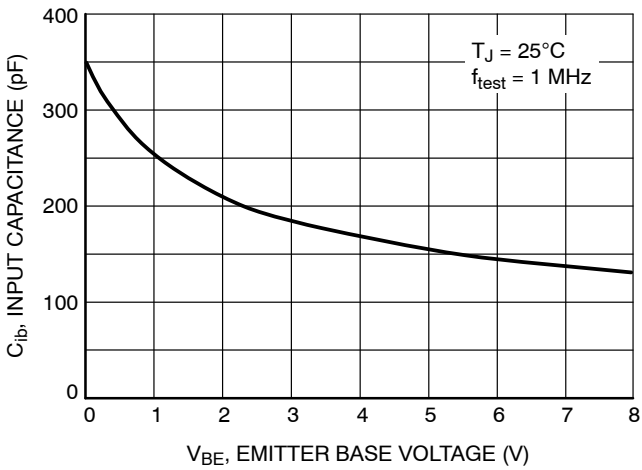


Figure 12. Input Capacitance

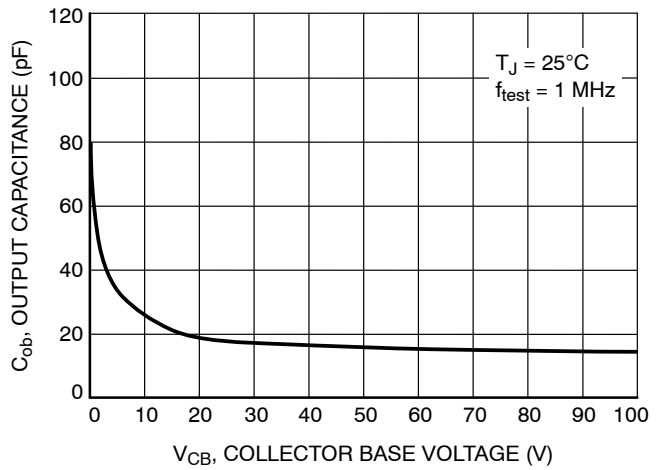


Figure 13. Output Capacitance

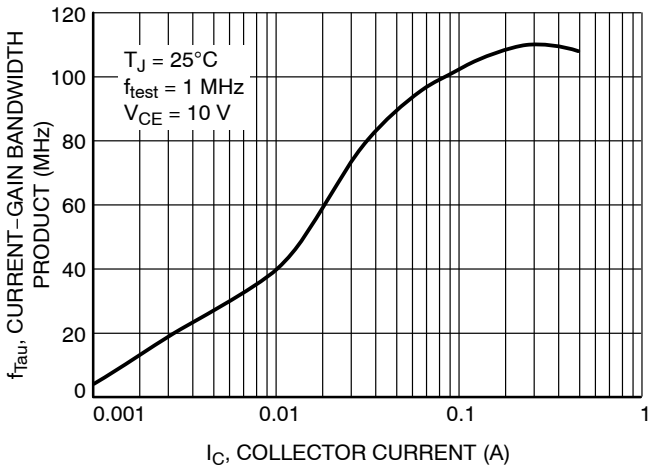


Figure 14. Current-Gain Bandwidth Product

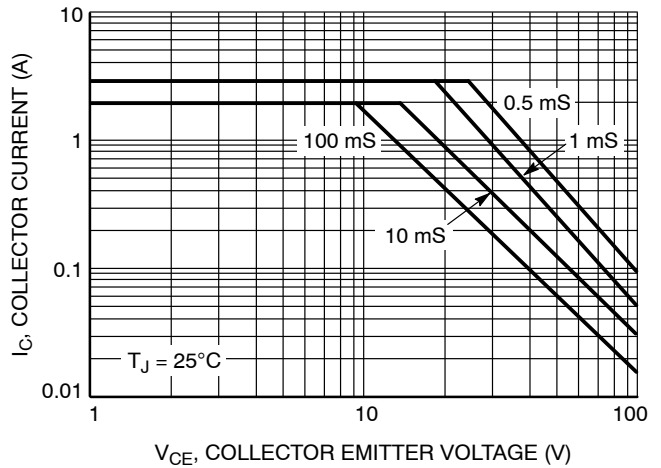


Figure 15. Safe Operating Area

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1

SOT-223 (TO-261)
CASE 318E-04
ISSUE R

DATE 02 OCT 2018



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	1.50	1.63	1.75
A1	0.02	0.06	0.10
b	0.60	0.75	0.89
b1	2.90	3.06	3.20
c	0.24	0.29	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	2.30 BSC		
L	0.20	---	---
L1	1.50	1.75	2.00
He	6.70	7.00	7.30
θ	0°	---	10°



DOCUMENT NUMBER:	98ASB42680B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-223 (TO-261)	PAGE 1 OF 2

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

SOT-223 (TO-261)
CASE 318E-04
ISSUE R

DATE 02 OCT 2018

- | | | | | |
|--|---|---|---|---|
| STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR | STYLE 2:
PIN 1. ANODE
2. CATHODE
3. NC
4. CATHODE | STYLE 3:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN | STYLE 4:
PIN 1. SOURCE
2. DRAIN
3. GATE
4. DRAIN | STYLE 5:
PIN 1. DRAIN
2. GATE
3. SOURCE
4. GATE |
| STYLE 6:
PIN 1. RETURN
2. INPUT
3. OUTPUT
4. INPUT | STYLE 7:
PIN 1. ANODE 1
2. CATHODE
3. ANODE 2
4. CATHODE | STYLE 8:
CANCELLED | STYLE 9:
PIN 1. INPUT
2. GROUND
3. LOGIC
4. GROUND | STYLE 10:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE |
| STYLE 11:
PIN 1. MT 1
2. MT 2
3. GATE
4. MT 2 | STYLE 12:
PIN 1. INPUT
2. OUTPUT
3. NC
4. OUTPUT | STYLE 13:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR | | |

**GENERIC
 MARKING DIAGRAM***



- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98ASB42680B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-223 (TO-261)	PAGE 2 OF 2

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales